

Vishay Siliconix

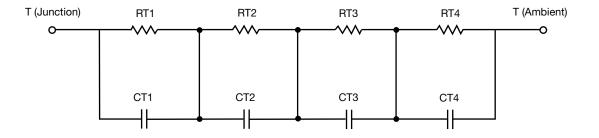
## **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	N/A	229.2554m	N/A			
RT2	N/A	462.6216m	N/A			
RT3	N/A	565.4507m	N/A			
RT4	N/A	546.6005m	N/A			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	N/A	158.9873m	N/A			
CT2	N/A	9.2544m	N/A			
CT3	N/A	1.2095m	N/A			
CT4	N/A	58.2244m	N/A			

Note

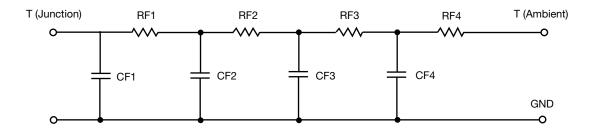
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	N/A	806.6971m	N/A		
RF2	N/A	667.0262m	N/A		
RF3	N/A	5.1677m	N/A		
RF4	N/A	316.8975m	N/A		
·	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	1.0909m	N/A		
CF2	N/A	13.3864m	N/A		
CF3	N/A	8.8367m	N/A		
CF4	N/A	89.3398m	N/A		

Note

• n/a indicates not applicable



# SiHD\_U3N50D\_RC

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